Date/Time: 12/15/2009 9:36:58 AM

Test Laboratory: Compliance Certification Services

GSM850 HAC_ER_Device

DUT: Palm; Type: P121UNA; Serial: 8054

Communication System: GSM850; Frequency: 824.2 MHz;Duty Cycle: 1:8
Medium parameters used: σ = 0 mho/m, ε_r = 1; ρ = 1000 kg/m^3
Phantom section: RF Section

DASY4 Configuration:
- Probe: ER3DV6 - SN2339; ConvF(1, 1, 1); Calibrated: 2/9/2009
- Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn500; Calibrated: 9/15/2009
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 100x
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

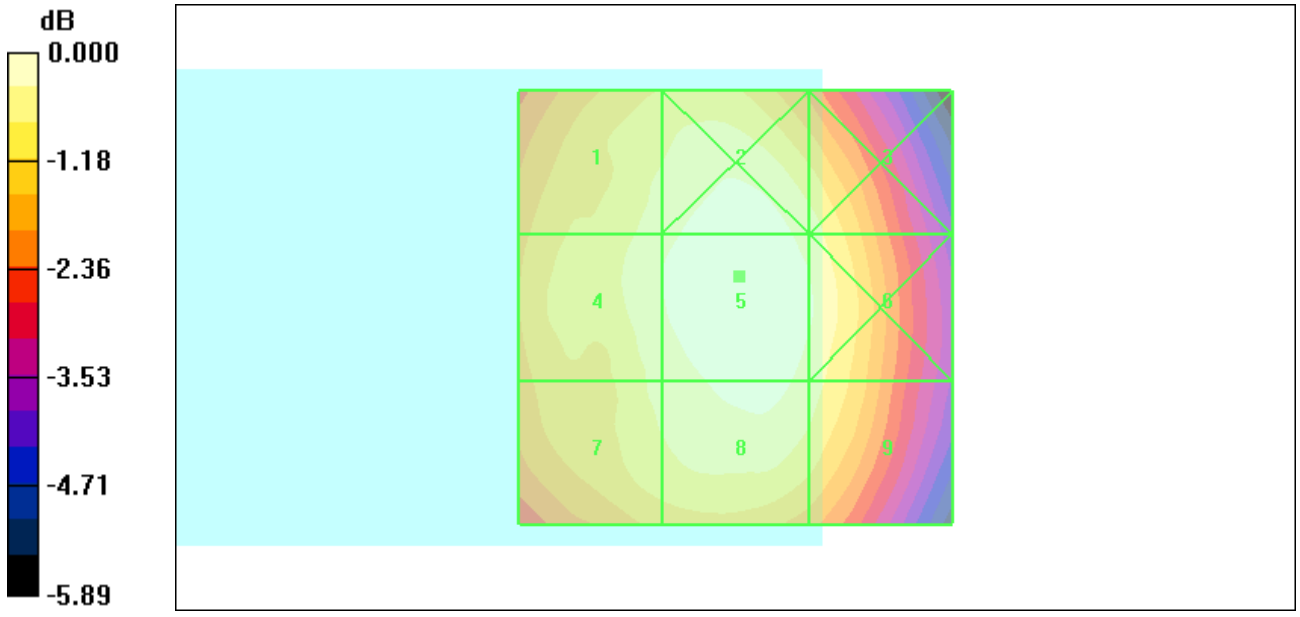
E Scan - L-ch/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 223.4 V/m
Probe Modulation Factor = 2.98
Device Reference Point: 0.000, 0.000, -6.30 mm
Reference Value = 99.4 V/m; Power Drift = -0.023 dB
Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak E-field in V/m

Grid 1 **209.8 M3**	Grid 2 **219.9 M3**	Grid 3 **209.3 M3**
Grid 4 **213.6 M3**	Grid 5 **223.4 M3**	Grid 6 **214.9 M3**
Grid 7 **207.3 M3**	Grid 8 **216.8 M3**	Grid 9 **209.2 M3**

Cursor:
Total = 223.4 V/m
E Category: M3
Location: -0.5, -3.5, 8.7 mm



0 dB = 223.4V/m

Date/Time: 12/15/2009 9:45:44 AM

Test Laboratory: Compliance Certification Services

GSM850 HAC_ER_Device

DUT: Palm; Type: P121UNA; Serial: 8054

Communication System: GSM850; Frequency: 836.6 MHz;Duty Cycle: 1:8
Medium parameters used: σ = 0 mho/m, ε_r = 1; ρ = 1000 kg/m^3
Phantom section: RF Section

DASY4 Configuration:
- Probe: ER3DV6 - SN2339; ConvF(1, 1, 1); Calibrated: 2/9/2009
- Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn500; Calibrated: 9/15/2009
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 100x
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

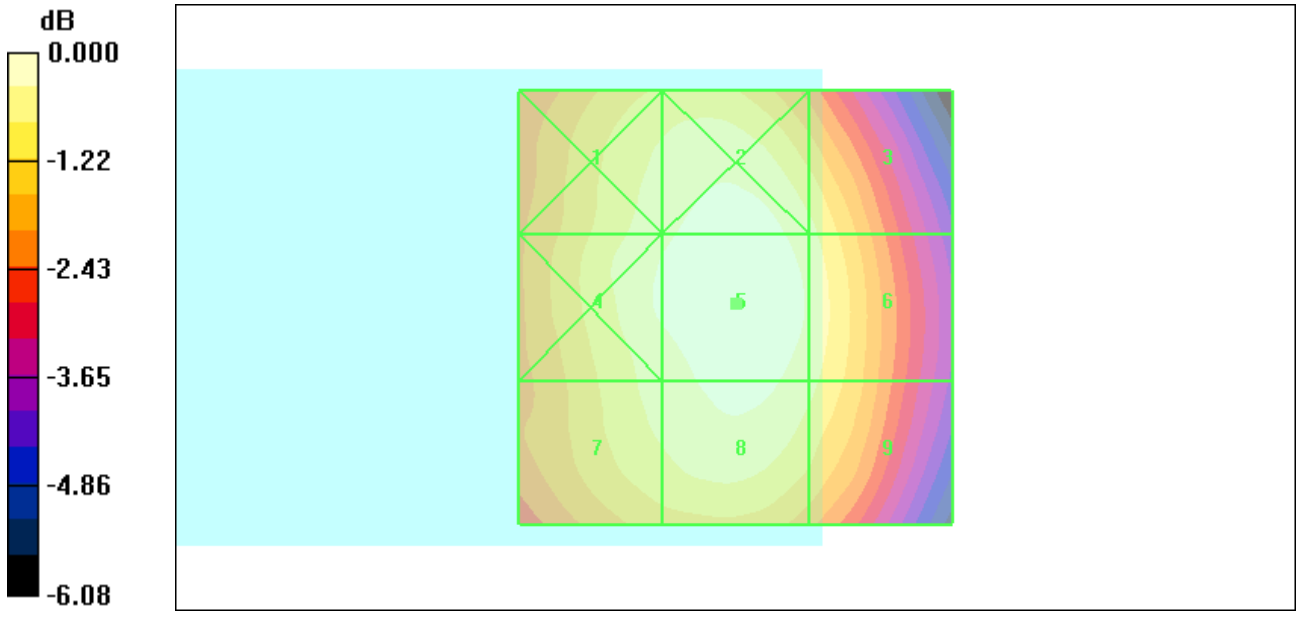
E Scan - M-ch/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 236.3 V/m
Probe Modulation Factor = 2.98
Device Reference Point: 0.000, 0.000, -6.30 mm
Reference Value = 104.5 V/m; Power Drift = 0.065 dB
Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak E-field in V/m

Grid 1 **222.9 M3**	Grid 2 **231.3 M3**	Grid 3 **218.6 M3**
Grid 4 **227.6 M3**	Grid 5 **236.3 M3**	Grid 6 **224.1 M3**
Grid 7 **220.3 M3**	Grid 8 **228.8 M3**	Grid 9 **218.4 M3**

Cursor:
Total = 236.3 V/m
E Category: M3
Location: 0, -0.5, 8.7 mm



0 dB = 236.3V/m

Date/Time: 12/15/2009 9:51:04 AM

Test Laboratory: Compliance Certification Services

GSM850 HAC_ER_Device

DUT: Palm; Type: P121UNA; Serial: 8054

Communication System: GSM850; Frequency: 848.8 MHz;Duty Cycle: 1:8
Medium parameters used: σ = 0 mho/m, ε_r = 1; ρ = 1000 kg/m^3
Phantom section: RF Section

DASY4 Configuration:
- Probe: ER3DV6 - SN2339; ConvF(1, 1, 1); Calibrated: 2/9/2009
- Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn500; Calibrated: 9/15/2009
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 100x
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

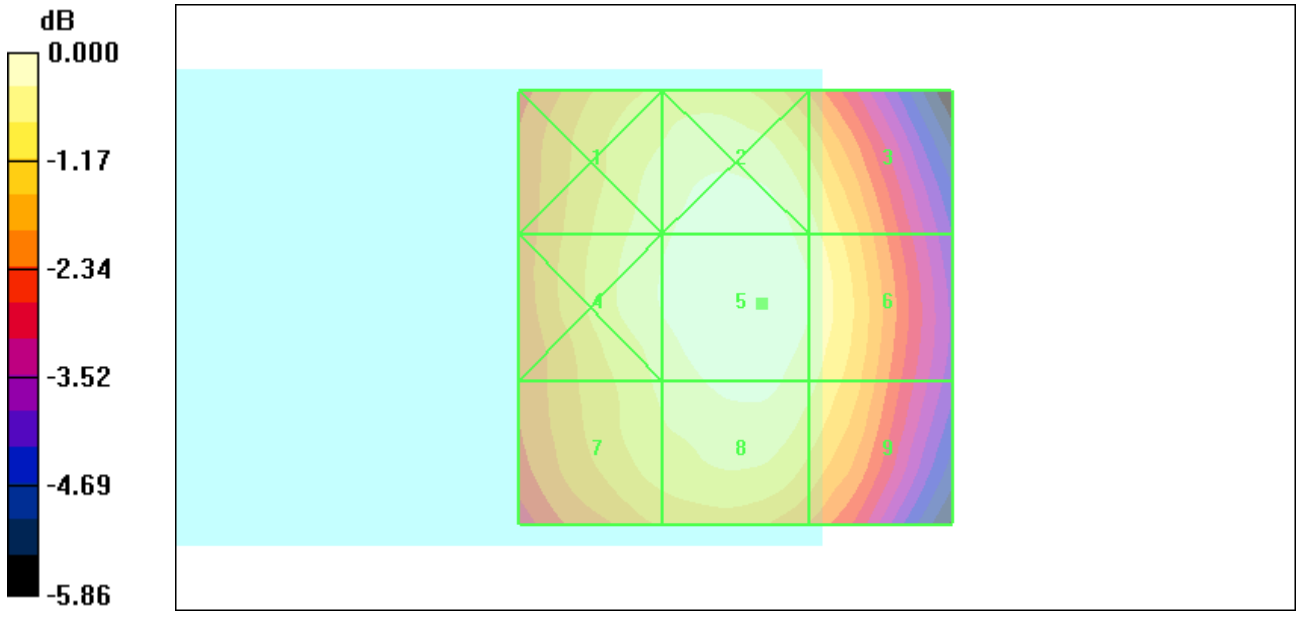
E Scan - H-ch/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 236.0 V/m
Probe Modulation Factor = 2.98
Device Reference Point: 0.000, 0.000, -6.30 mm
Reference Value = 104.8 V/m; Power Drift = 0.019 dB
Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak E-field in V/m

Grid 1 **223.2 M3**	Grid 2 **232.8 M3**	Grid 3 **220.3 M3**
Grid 4 **226.6 M3**	Grid 5 **236.0 M3**	Grid 6 **226.1 M3**
Grid 7 **218.0 M3**	Grid 8 **228.0 M3**	Grid 9 **218.5 M3**

Cursor:
Total = 236.0 V/m
E Category: M3
Location: -3, -0.5, 8.7 mm



0 dB = 236.0V/m

Date/Time: 12/15/2009 3:45:35 PM

Test Laboratory: Compliance Certification Services

GSM850 HAC_ER_Device with inductive cover

DUT: Palm; Type: P121UNA; Serial: 8054

Communication System: GSM850; Frequency: 824.2 MHz;Duty Cycle: 1:8
Medium parameters used: σ = 0 mho/m, ε_r = 1; ρ = 1000 kg/m^3
Phantom section: RF Section

DASY4 Configuration:
- Probe: ER3DV6 - SN2339; ConvF(1, 1, 1); Calibrated: 2/9/2009
- Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn500; Calibrated: 9/15/2009
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 100x
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - L-ch/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

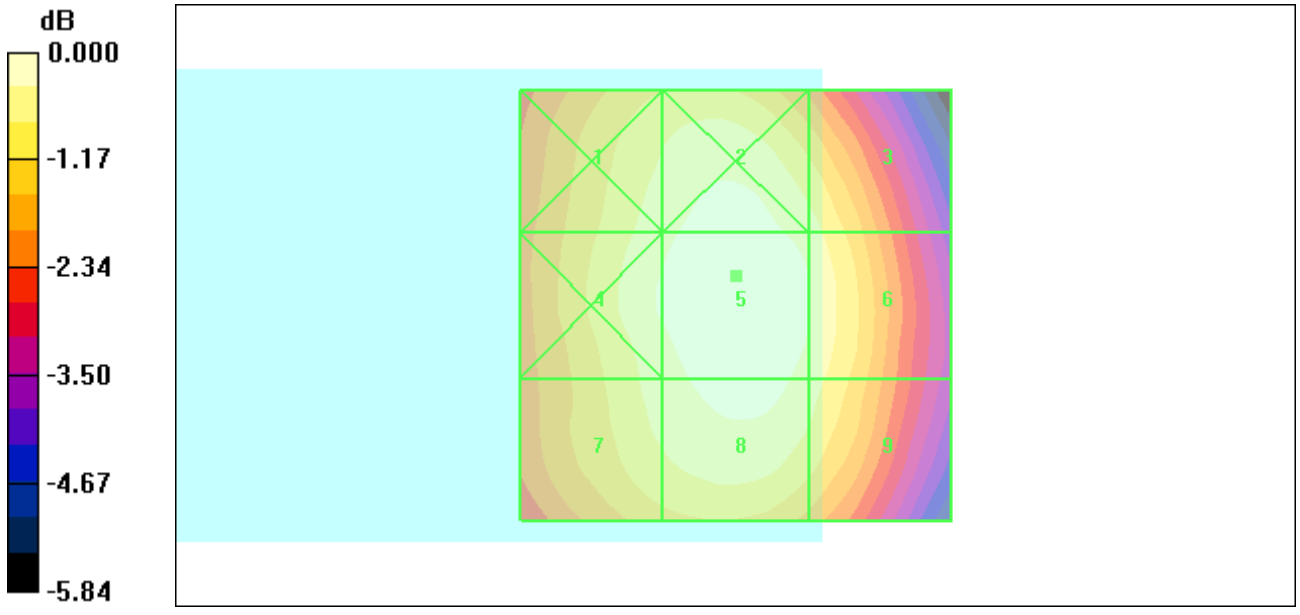
Maximum value of peak Total field = 213.7 V/m
Probe Modulation Factor = 2.98
Device Reference Point: 0.000, 0.000, -6.30 mm
Reference Value = 93.9 V/m; Power Drift = -0.036 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak E-field in V/m

Grid 1 **201.4 M3**	Grid 2 **210.1 M3**	Grid 3 **199.6 M3**
Grid 4 **205.7 M3**	Grid 5 **213.7 M3**	Grid 6 **204.6 M3**
Grid 7 **200.1 M3**	Grid 8 **208.3 M3**	Grid 9 **200.2 M3**

Cursor:
Total = 213.7 V/m
E Category: M3
Location: 0, -3.5, 8.7 mm



0 dB = 213.7V/m

Date/Time: 12/15/2009 3:51:06 PM

Test Laboratory: Compliance Certification Services

GSM850 HAC_ER_Device with inductive cover

DUT: Palm; Type: P121UNA; Serial: 8054

Communication System: GSM850; Frequency: 836.6 MHz;Duty Cycle: 1:8
Medium parameters used: σ = 0 mho/m, ε_r = 1; ρ = 1000 kg/m^3
Phantom section: RF Section

DASY4 Configuration:
- Probe: ER3DV6 - SN2339; ConvF(1, 1, 1); Calibrated: 2/9/2009
- Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn500; Calibrated: 9/15/2009
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 100x
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - M-ch/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

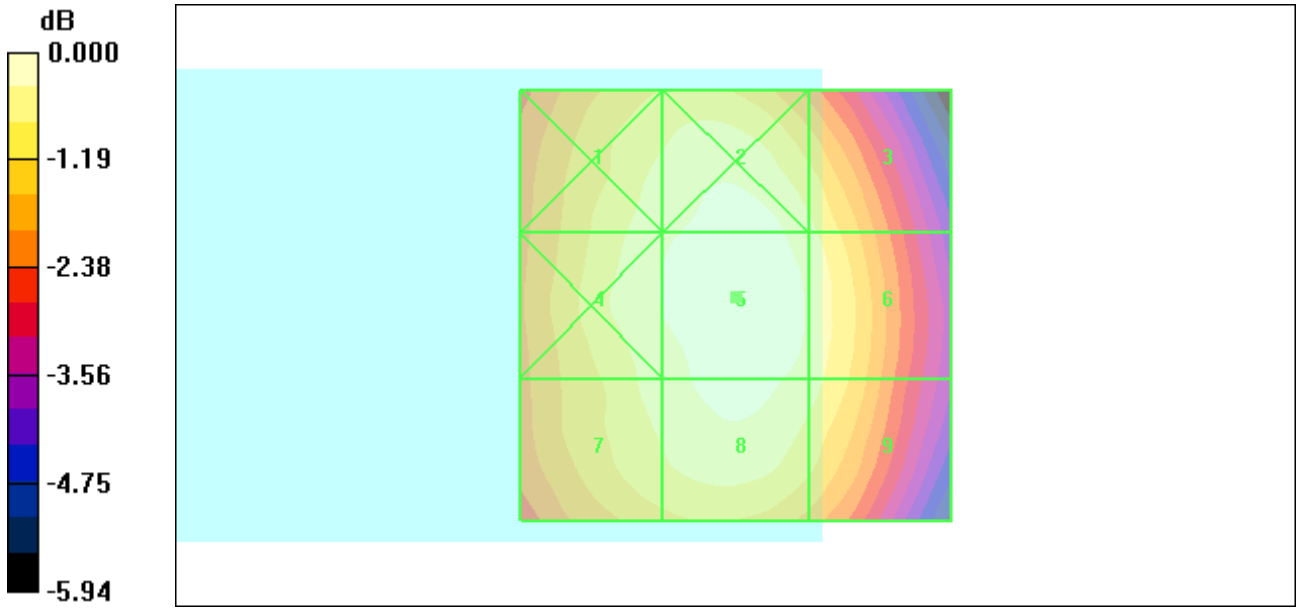
Maximum value of peak Total field = 226.1 V/m
Probe Modulation Factor = 2.98
Device Reference Point: 0.000, 0.000, -6.30 mm
Reference Value = 99.3 V/m; Power Drift = 0.019 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak E-field in V/m

Grid 1 **213.2 M3**	Grid 2 **221.4 M3**	Grid 3 **209.3 M3**
Grid 4 **216.7 M3**	Grid 5 **226.1 M3**	Grid 6 **214.7 M3**
Grid 7 **211.6 M3**	Grid 8 **219.9 M3**	Grid 9 **211.0 M3**

Cursor:
Total = 226.1 V/m
E Category: M3
Location: 0, -1, 8.7 mm



0 dB = 226.1V/m

Date/Time: 12/15/2009 3:57:42 PM

Test Laboratory: Compliance Certification Services

GSM850 HAC_ER_Device with inductive cover

DUT: Palm; Type: P121UNA; Serial: 8054

Communication System: GSM850; Frequency: 848.8 MHz;Duty Cycle: 1:8
Medium parameters used: σ = 0 mho/m, ε_r = 1; ρ = 1000 kg/m^3
Phantom section: RF Section

DASY4 Configuration:
- Probe: ER3DV6 - SN2339; ConvF(1, 1, 1); Calibrated: 2/9/2009
- Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn500; Calibrated: 9/15/2009
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 100x
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - H-ch/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

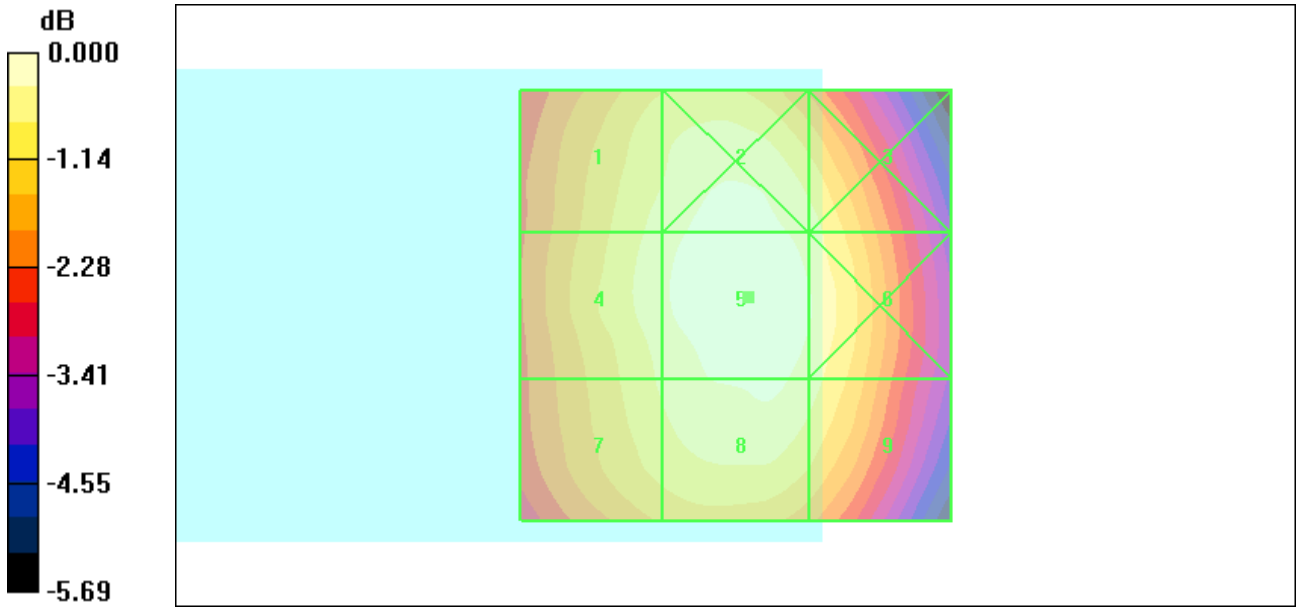
Maximum value of peak Total field = 222.6 V/m
Probe Modulation Factor = 2.95
Device Reference Point: 0.000, 0.000, -6.30 mm
Reference Value = 98.8 V/m; Power Drift = 0.024 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak E-field in V/m

Grid 1 **208.3 M3**	Grid 2 **218.1 M3**	Grid 3 **208.6 M3**
Grid 4 **211.3 M3**	Grid 5 **222.6 M3**	Grid 6 **214.2 M3**
Grid 7 **205.6 M3**	Grid 8 **215.7 M3**	Grid 9 **208.5 M3**

Cursor:
Total = 222.6 V/m
E Category: M3
Location: -1.5, -1, 8.7 mm



0 dB = 222.6V/m

Date/Time: 12/15/2009 10:04:09 AM

Test Laboratory: Compliance Certification Services

GSM1900 HAC_ER_Device

DUT: Palm; Type: P121UNA; Serial: 8054

Communication System: DCS 1900; Frequency: 1850.2 MHz;Duty Cycle: 1:8
Medium parameters used: σ = 0 mho/m, ε_r = 1; ρ = 1000 kg/m^3
Phantom section: RF Section

DASY4 Configuration:
- Probe: ER3DV6 - SN2339; ConvF(1, 1, 1); Calibrated: 2/9/2009
- Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn500; Calibrated: 9/15/2009
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 100x
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

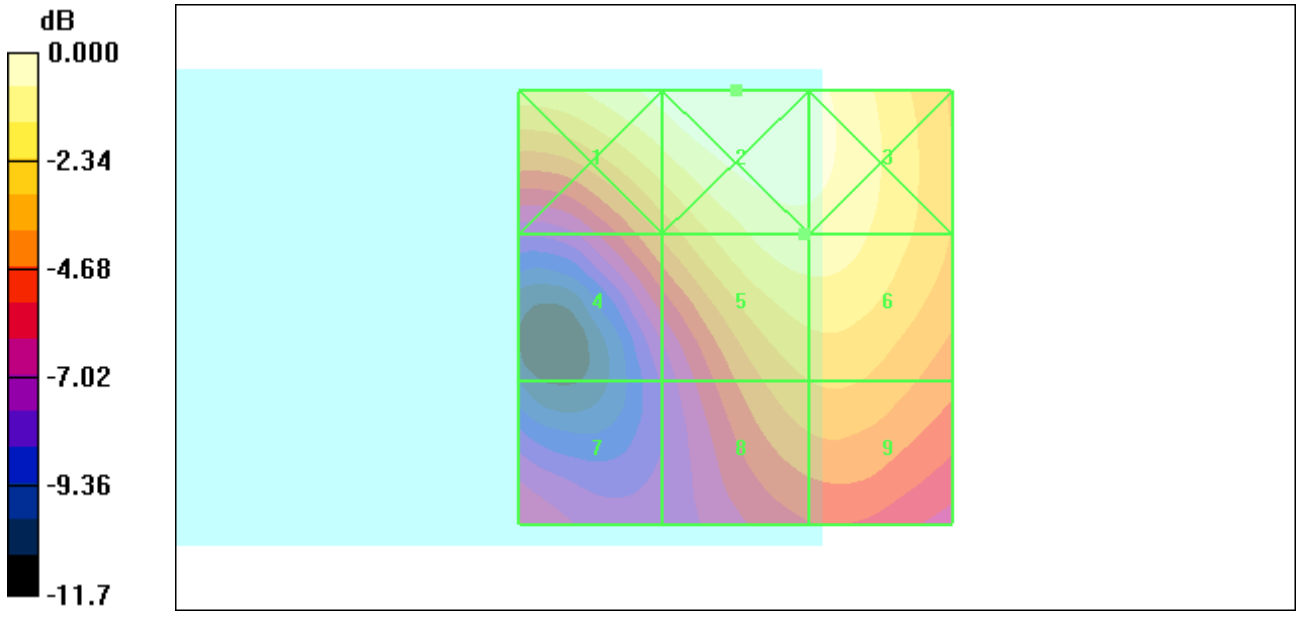
E Scan - L-ch/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 81.5 V/m
Probe Modulation Factor = 2.75
Device Reference Point: 0.000, 0.000, -6.30 mm
Reference Value = 28.6 V/m; Power Drift = -0.187 dB
Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak E-field in V/m

Grid 1 **87.0 M2**	Grid 2 **92.0 M2**	Grid 3 **87.6 M2**
Grid 4 **59.9 M3**	Grid 5 **81.5 M3**	Grid 6 **81.5 M3**
Grid 7 **45.4 M4**	Grid 8 **64.3 M3**	Grid 9 **65.1 M3**

Cursor:
Total = 92.0 V/m
E Category: M2
Location: 0, -25, 8.7 mm



0 dB = 92.0V/m

Date/Time: 12/15/2009 10:09:18 AM

Test Laboratory: Compliance Certification Services

GSM1900 HAC_ER_Device

DUT: Palm; Type: P121UNA; Serial: 8054

Communication System: DCS 1900; Frequency: 1880 MHz;Duty Cycle: 1:8
Medium parameters used: σ = 0 mho/m, ε_r = 1; ρ = 1000 kg/m^3
Phantom section: RF Section

DASY4 Configuration:
- Probe: ER3DV6 - SN2339; ConvF(1, 1, 1); Calibrated: 2/9/2009
- Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn500; Calibrated: 9/15/2009
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 100x
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

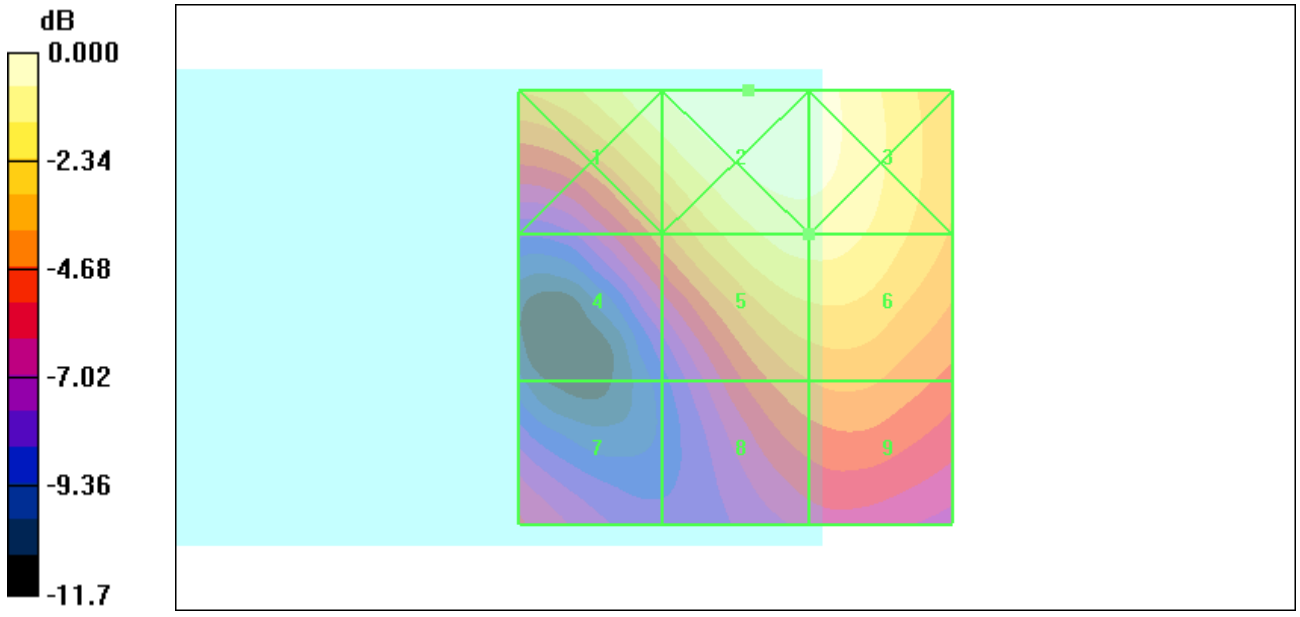
E Scan - M-ch/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 81.1 V/m
Probe Modulation Factor = 2.75
Device Reference Point: 0.000, 0.000, -6.30 mm
Reference Value = 26.5 V/m; Power Drift = -0.014 dB
Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak E-field in V/m

Grid 1 **84.8 M2**	Grid 2 **92.8 M2**	Grid 3 **89.1 M2**
Grid 4 **57.5 M3**	Grid 5 **81.1 M3**	Grid 6 **81.1 M3**
Grid 7 **46.1 M4**	Grid 8 **59.2 M3**	Grid 9 **60.7 M3**

Cursor:
Total = 92.8 V/m
E Category: M2
Location: -1.5, -25, 8.7 mm



0 dB = 92.8V/m

Date/Time: 12/15/2009 10:14:46 AM

Test Laboratory: Compliance Certification Services

GSM1900 HAC_ER_Device

DUT: Palm; Type: P121UNA; Serial: 8054

Communication System: DCS 1900; Frequency: 1909.8 MHz;Duty Cycle: 1:8
Medium parameters used: σ = 0 mho/m, ε_r = 1; ρ = 1000 kg/m^3
Phantom section: RF Section

DASY4 Configuration:
- Probe: ER3DV6 - SN2339; ConvF(1, 1, 1); Calibrated: 2/9/2009
- Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn500; Calibrated: 9/15/2009
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 100x
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

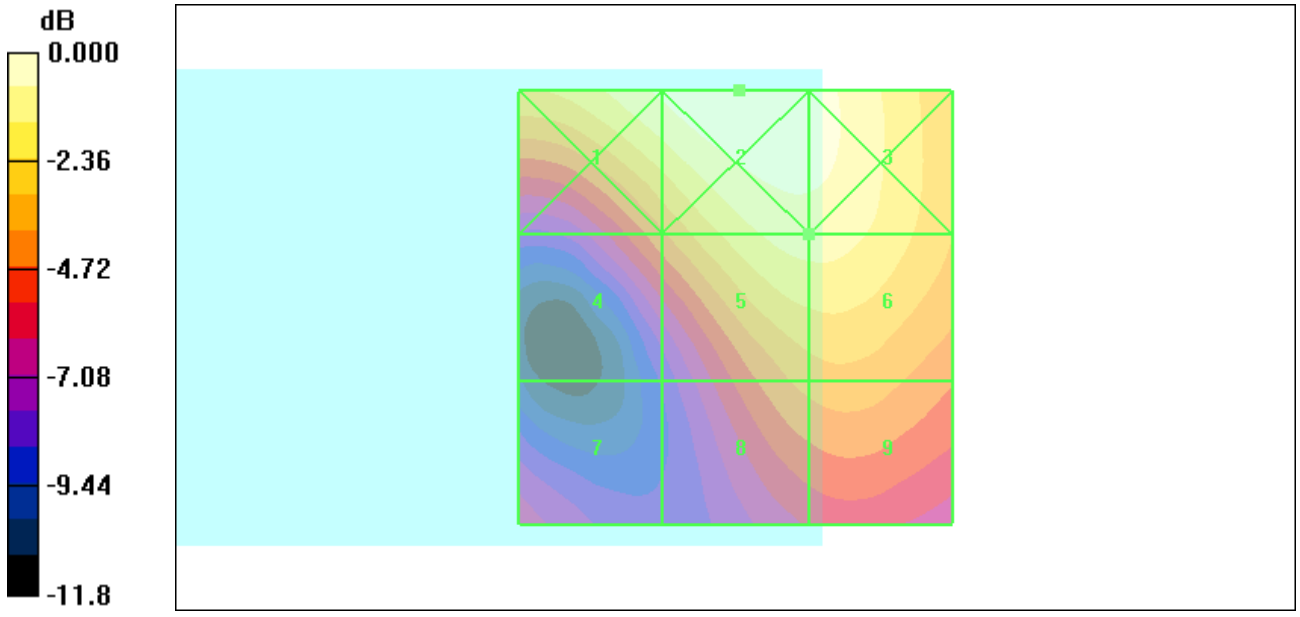
E Scan - H-ch/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 75.2 V/m
Probe Modulation Factor = 2.75
Device Reference Point: 0.000, 0.000, -6.30 mm
Reference Value = 24.9 V/m; Power Drift = 0.003 dB
Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak E-field in V/m

Grid 1 **80.4 M3**	Grid 2 **86.4 M2**	Grid 3 **82.6 M3**
Grid 4 **54.1 M3**	Grid 5 **75.2 M3**	Grid 6 **75.2 M3**
Grid 7 **40.5 M4**	Grid 8 **56.9 M3**	Grid 9 **58.3 M3**

Cursor:
Total = 86.4 V/m
E Category: M2
Location: -0.5, -25, 8.7 mm



0 dB = 86.4V/m

Date/Time: 12/15/2009 3:19:50 PM

Test Laboratory: Compliance Certification Services

GSM1900 HAC_ER_Device_Final

DUT: Palm; Type: P121UNA; Serial: 8054

Communication System: DCS 1900; Frequency: 1850.2 MHz;Duty Cycle: 1:8
Medium parameters used: σ = 0 mho/m, ε_r = 1; ρ = 1000 kg/m^3
Phantom section: RF Section

DASY4 Configuration:
- Probe: ER3DV6 - SN2339; ConvF(1, 1, 1); Calibrated: 2/9/2009
- Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn500; Calibrated: 9/15/2009
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 100x
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

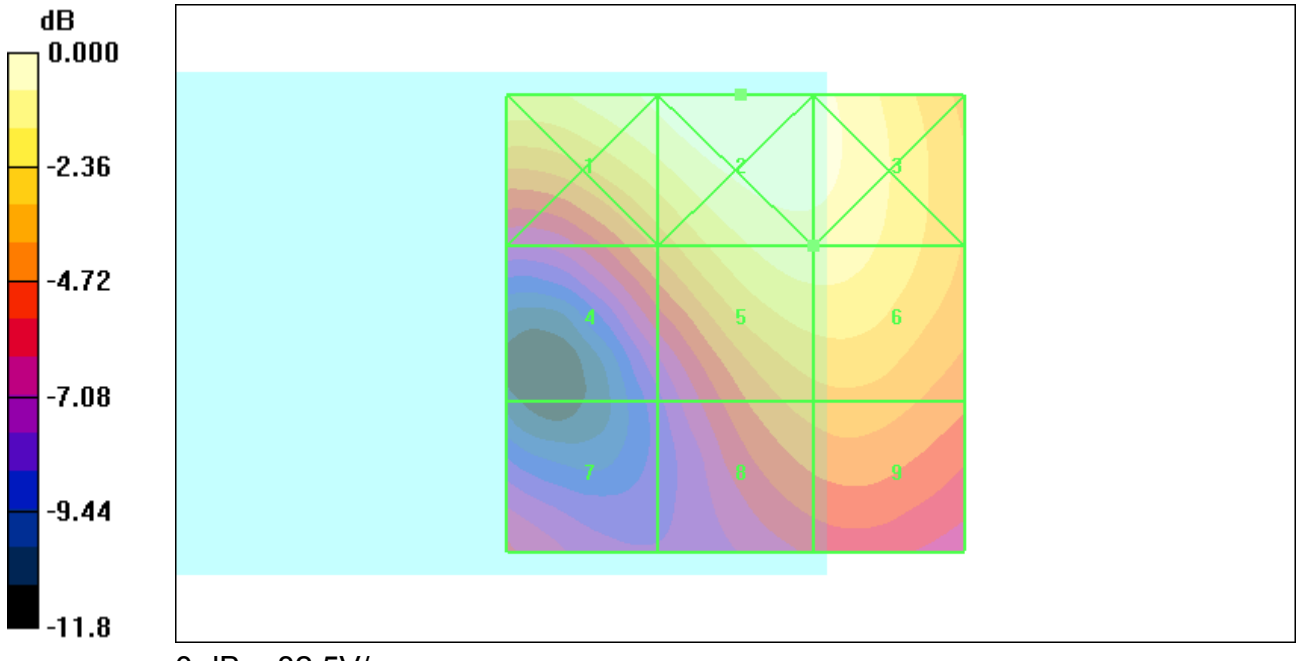
E Scan - L-ch/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 72.5 V/m
Probe Modulation Factor = 2.75
Device Reference Point: 0.000, 0.000, -6.30 mm
Reference Value = 25.5 V/m; Power Drift = -0.050 dB
Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak E-field in V/m

Grid 1 **77.2 M3**	Grid 2 **82.5 M3**	Grid 3 **78.5 M3**
Grid 4 **53.9 M3**	Grid 5 **72.5 M3**	Grid 6 **72.5 M3**
Grid 7 **40.9 M4**	Grid 8 **55.0 M3**	Grid 9 **56.1 M3**

Cursor:
Total = 82.5 V/m
E Category: M3
Location: -0.5, -25, 8.7 mm



0 dB = 82.5V/m

Date/Time: 12/15/2009 3:25:18 PM

Test Laboratory: Compliance Certification Services

GSM1900 HAC_ER_Device_Final

DUT: Palm; Type: P121UNA; Serial: 8054

Communication System: DCS 1900; Frequency: 1880 MHz;Duty Cycle: 1:8
Medium parameters used: σ = 0 mho/m, ε_r = 1; ρ = 1000 kg/m^3
Phantom section: RF Section

DASY4 Configuration:
- Probe: ER3DV6 - SN2339; ConvF(1, 1, 1); Calibrated: 2/9/2009
- Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn500; Calibrated: 9/15/2009
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 100x
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - M-ch/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

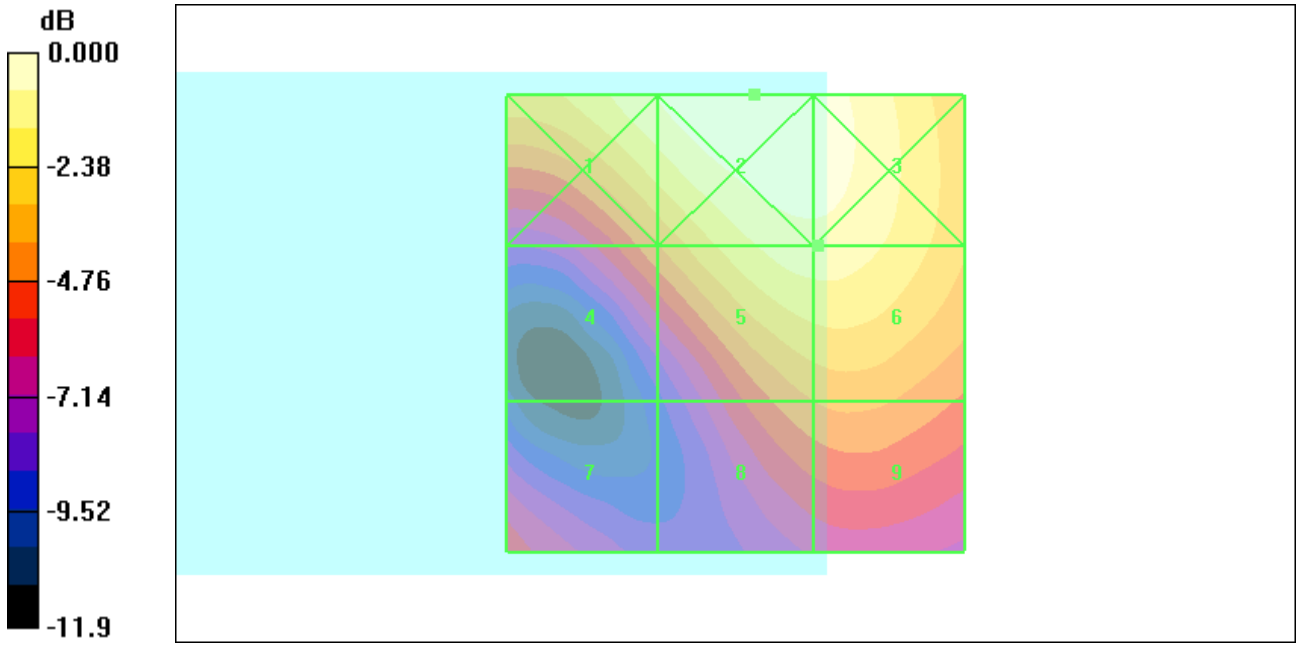
Maximum value of peak Total field = 72.7 V/m
Probe Modulation Factor = 2.75
Device Reference Point: 0.000, 0.000, -6.30 mm
Reference Value = 24.0 V/m; Power Drift = -0.017 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak E-field in V/m

Grid 1 **76.0 M3**	Grid 2 **82.5 M3**	Grid 3 **79.9 M3**
Grid 4 **51.9 M3**	Grid 5 **72.6 M3**	Grid 6 **72.7 M3**
Grid 7 **42.2 M4**	Grid 8 **52.3 M3**	Grid 9 **53.7 M3**

Cursor:
Total = 82.5 V/m
E Category: M3
Location: -2, -25, 8.7 mm



0 dB = 82.5V/m

Date/Time: 12/15/2009 3:30:32 PM

Test Laboratory: Compliance Certification Services

GSM1900 HAC_ER_Device_Final

DUT: Palm; Type: P121UNA; Serial: 8054

Communication System: DCS 1900; Frequency: 1909.8 MHz;Duty Cycle: 1:8
Medium parameters used: σ = 0 mho/m, ε_r = 1; ρ = 1000 kg/m^3
Phantom section: RF Section

DASY4 Configuration:
- Probe: ER3DV6 - SN2339; ConvF(1, 1, 1); Calibrated: 2/9/2009
- Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn500; Calibrated: 9/15/2009
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 100x
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - H-ch/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

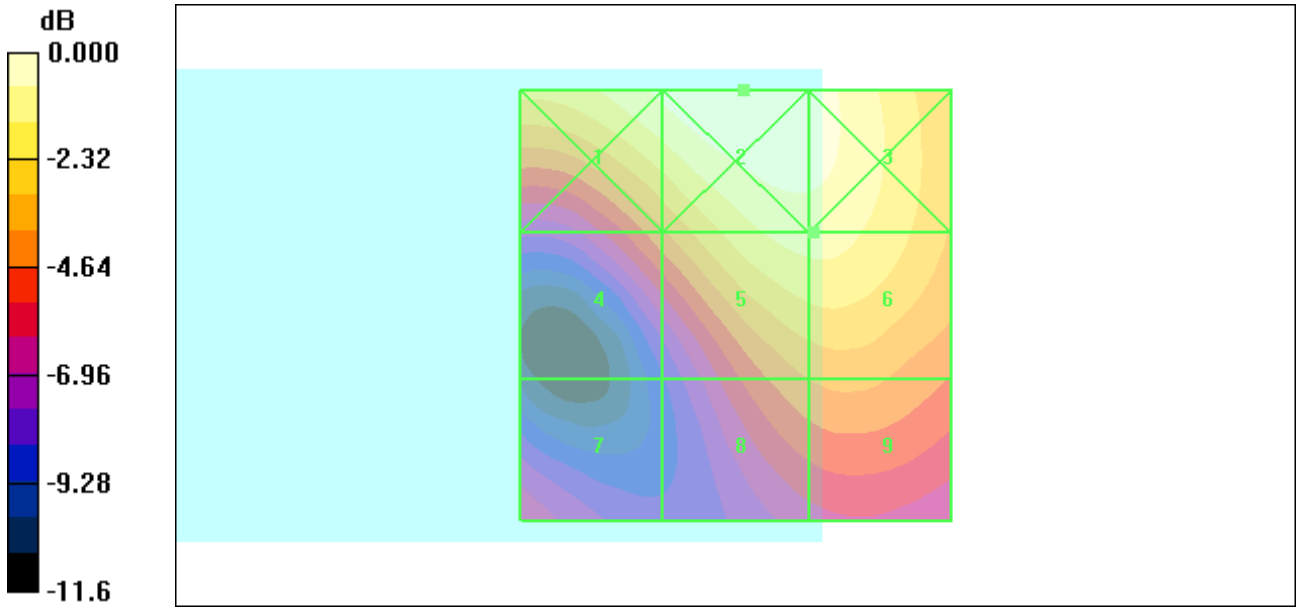
Maximum value of peak Total field = 69.5 V/m
Probe Modulation Factor = 2.75
Device Reference Point: 0.000, 0.000, -6.30 mm
Reference Value = 23.2 V/m; Power Drift = 0.028 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak E-field in V/m

Grid 1 **74.6 M3**	Grid 2 **79.8 M3**	Grid 3 **76.6 M3**
Grid 4 **50.3 M3**	Grid 5 **69.5 M3**	Grid 6 **69.5 M3**
Grid 7 **38.8 M4**	Grid 8 **51.3 M3**	Grid 9 **52.7 M3**

Cursor:
Total = 79.8 V/m
E Category: M3
Location: -1, -25, 8.7 mm



0 dB = 79.8V/m

Date/Time: 12/15/2009 4:19:33 PM

Test Laboratory: Compliance Certification Services

GSM850 HAC_H3DV6_Device

DUT: Palm; Type: P121UNA; Serial: 8054

Communication System: GSM850; Frequency: 824.2 MHz;Duty Cycle: 1:8
Medium parameters used: σ = 0 mho/m, ε_r = 1; ρ = 1 kg/m^3
Phantom section: RF Section

DASY4 Configuration:
- Probe: H3DV6 - SN6157; ; Calibrated: 2/10/2009
- Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn500; Calibrated: 9/15/2009
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 100x
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - L-ch/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

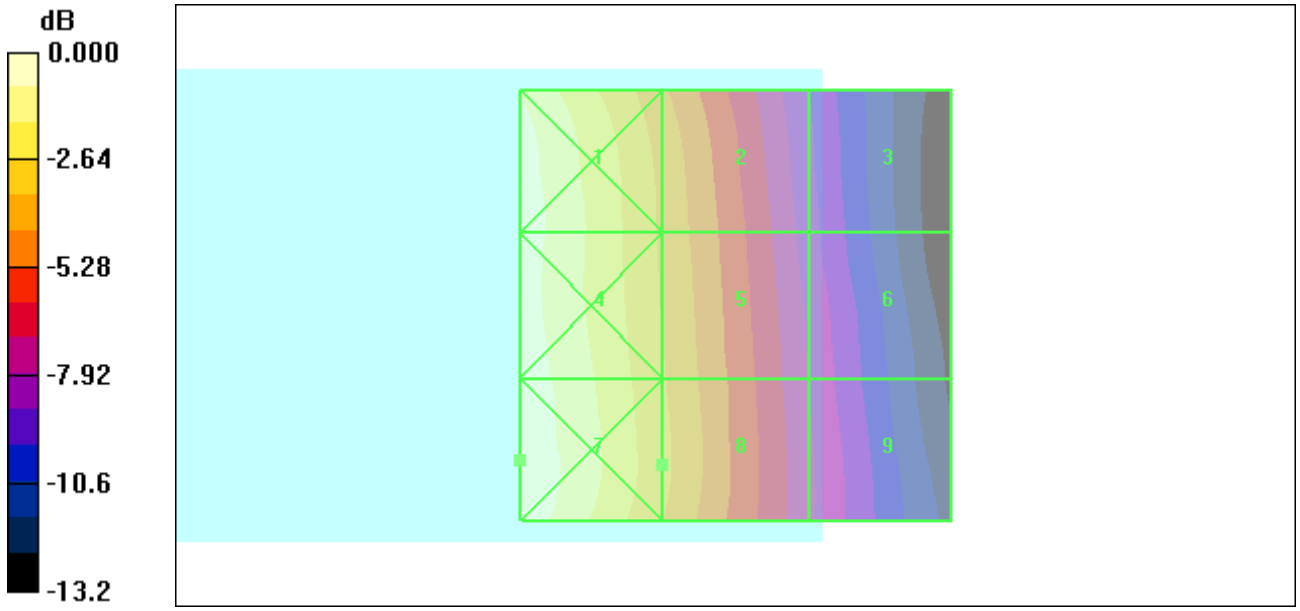
Maximum value of peak Total field = 0.324 A/m
Probe Modulation Factor = 2.85
Device Reference Point: 0.000, 0.000, -6.30 mm
Reference Value = 0.091 A/m; Power Drift = -0.040 dB

Hearing Aid Near-Field Category: M4 (AWF -5 dB)

Peak H-field in A/m

Grid 1 **0.453 M3**	Grid 2 **0.310 M4**	Grid 3 **0.180 M4**
Grid 4 **0.461 M3**	Grid 5 **0.319 M4**	Grid 6 **0.190 M4**
Grid 7 **0.472 M3**	Grid 8 **0.324 M4**	Grid 9 **0.195 M4**

Cursor:
Total = 0.472 A/m
H Category: M3
Location: 25, 18, 8.7 mm



0 dB = 0.472A/m

Date/Time: 12/15/2009 4:25:16 PM

Test Laboratory: Compliance Certification Services

GSM850 HAC_H3DV6_Device

DUT: Palm; Type: P121UNA; Serial: 8054

Communication System: GSM850; Frequency: 836.6 MHz;Duty Cycle: 1:8
Medium parameters used: σ = 0 mho/m, ε_r = 1; ρ = 1 kg/m^3
Phantom section: RF Section

DASY4 Configuration:
- Probe: H3DV6 - SN6157; ; Calibrated: 2/10/2009
- Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn500; Calibrated: 9/15/2009
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 100x
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - M-ch/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

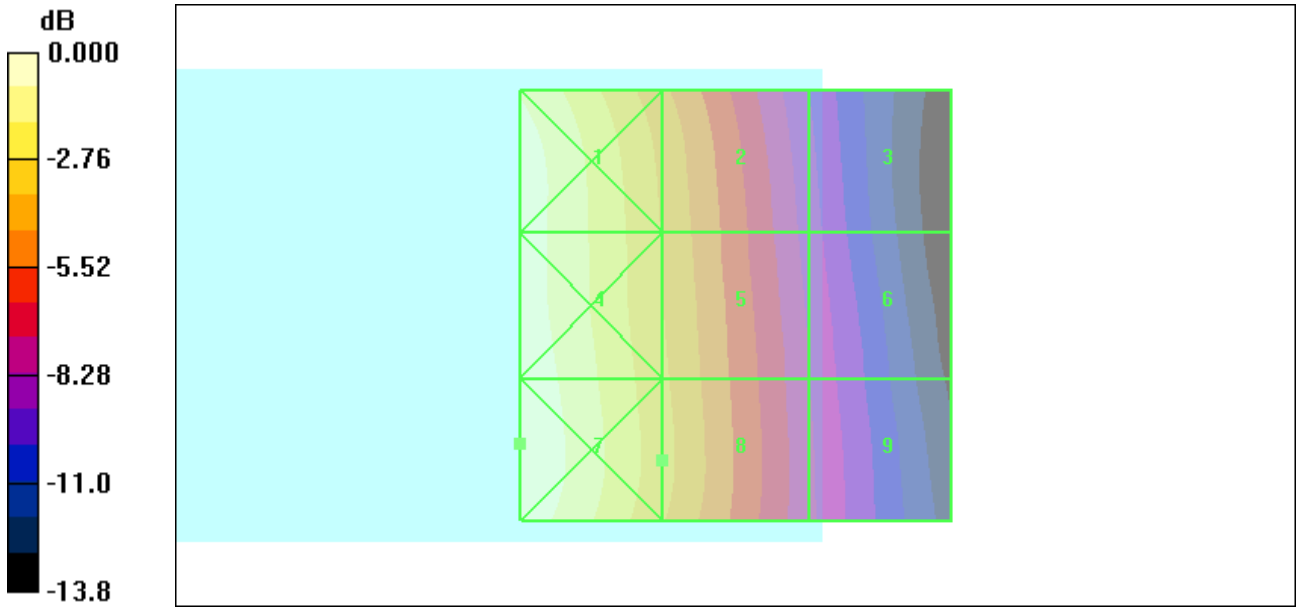
Maximum value of peak Total field = 0.342 A/m
Probe Modulation Factor = 2.85
Device Reference Point: 0.000, 0.000, -6.30 mm
Reference Value = 0.095 A/m; Power Drift = -0.083 dB

Hearing Aid Near-Field Category: M4 (AWF -5 dB)

Peak H-field in A/m

Grid 1 **0.482 M3**	Grid 2 **0.326 M4**	Grid 3 **0.185 M4**
Grid 4 **0.490 M3**	Grid 5 **0.336 M4**	Grid 6 **0.195 M4**
Grid 7 **0.501 M3**	Grid 8 **0.342 M4**	Grid 9 **0.199 M4**

Cursor:
Total = 0.501 A/m
H Category: M3
Location: 25, 16, 8.7 mm



0 dB = 0.501A/m

Date/Time: 12/15/2009 4:38:46 PM

Test Laboratory: Compliance Certification Services

GSM850 HAC_H3DV6_Device

DUT: Palm; Type: P121UNA; Serial: 8054

Communication System: GSM850; Frequency: 848.8 MHz;Duty Cycle: 1:8
Medium parameters used: σ = 0 mho/m, ε_r = 1; ρ = 1 kg/m^3
Phantom section: RF Section

DASY4 Configuration:
- Probe: H3DV6 - SN6157; ; Calibrated: 2/10/2009
- Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn500; Calibrated: 9/15/2009
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 100x
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - H-ch/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

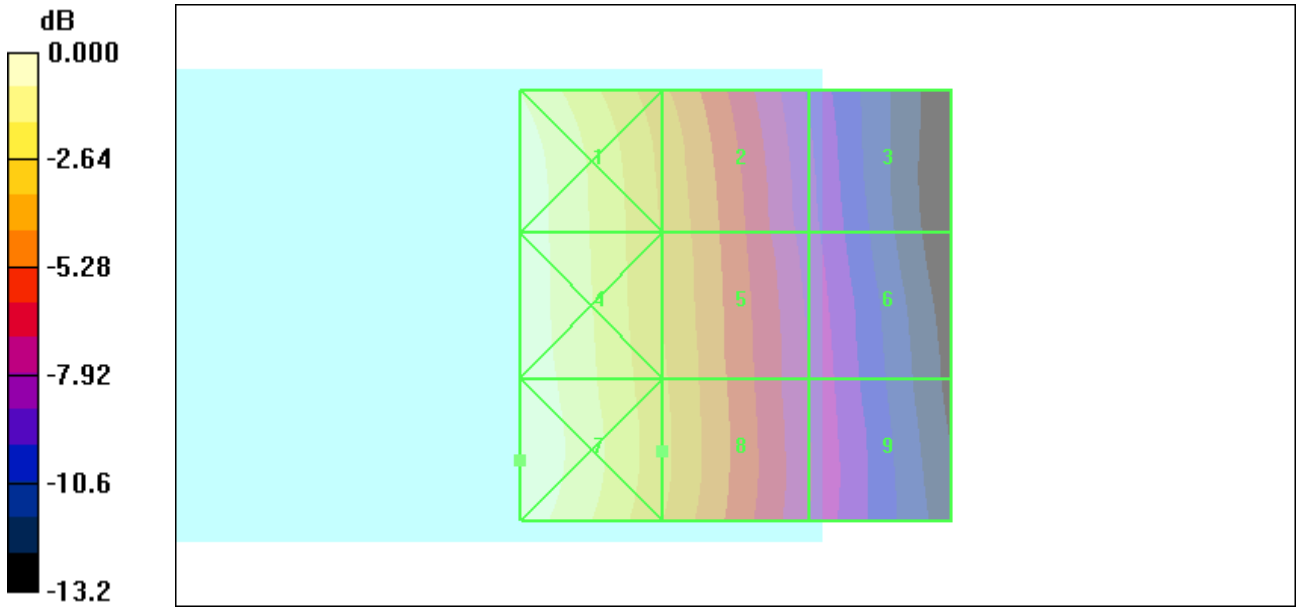
Maximum value of peak Total field = 0.355 A/m
Probe Modulation Factor = 2.85
Device Reference Point: 0.000, 0.000, -6.30 mm
Reference Value = 0.099 A/m; Power Drift = -0.051 dB

Hearing Aid Near-Field Category: M4 (AWF -5 dB)

Peak H-field in A/m

Grid 1 **0.497 M3**	Grid 2 **0.341 M4**	Grid 3 **0.197 M4**
Grid 4 **0.505 M3**	Grid 5 **0.350 M4**	Grid 6 **0.207 M4**
Grid 7 **0.515 M3**	Grid 8 **0.355 M4**	Grid 9 **0.211 M4**

Cursor:
Total = 0.515 A/m
H Category: M3
Location: 25, 18, 8.7 mm



0 dB = 0.515A/m

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Test Laboratory: Compliance Certification Services

GSM850 HAC_H3DV6_Device With Inductive Cover

DUT: Palm; Type: P121UNA; Serial: 8054

Communication System: GSM850; Frequency: 824.2 MHz;Duty Cycle: 1:8
Medium parameters used: σ = 0 mho/m, ε_r = 1; ρ = 1 kg/m^3
Phantom section: RF Section

DASY4 Configuration:
- Probe: H3DV6 - SN6157; ; Calibrated: 2/10/2009
- Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn500; Calibrated: 9/15/2009
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 100x
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

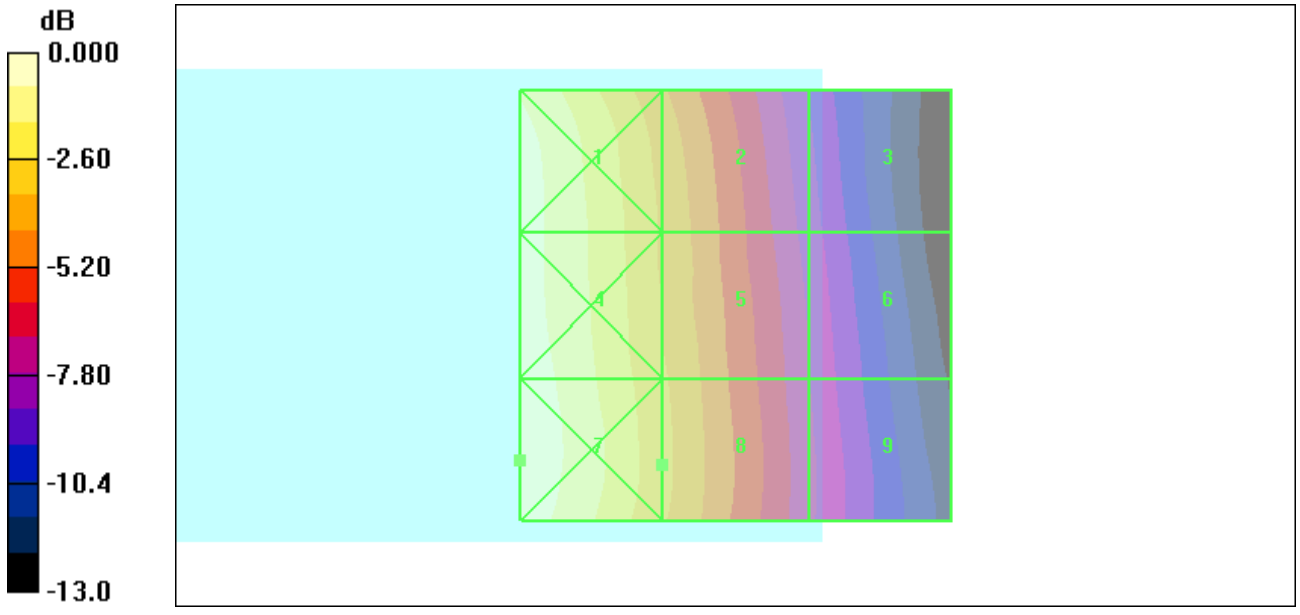
H Scan - L-ch/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.331 A/m
Probe Modulation Factor = 2.85
Device Reference Point: 0.000, 0.000, -6.30 mm
Reference Value = 0.093 A/m; Power Drift = 0.030 dB
Hearing Aid Near-Field Category: M4 (AWF -5 dB)

Peak H-field in A/m

Grid 1 **0.456 M3**	Grid 2 **0.316 M4**	Grid 3 **0.186 M4**
Grid 4 **0.466 M3**	Grid 5 **0.325 M4**	Grid 6 **0.196 M4**
Grid 7 **0.476 M3**	Grid 8 **0.331 M4**	Grid 9 **0.200 M4**

Cursor:
Total = 0.476 A/m
H Category: M3
Location: 25, 18, 8.7 mm



0 dB = 0.476A/m

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Test Laboratory: Compliance Certification Services

GSM850 HAC_H3DV6_Device With Inductive Cover

DUT: Palm; Type: P121UNA; Serial: 8054

Communication System: GSM850; Frequency: 836.6 MHz;Duty Cycle: 1:8
Medium parameters used: σ = 0 mho/m, ε_r = 1; ρ = 1 kg/m^3
Phantom section: RF Section

DASY4 Configuration:
- Probe: H3DV6 - SN6157; ; Calibrated: 2/10/2009
- Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn500; Calibrated: 9/15/2009
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 100x
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

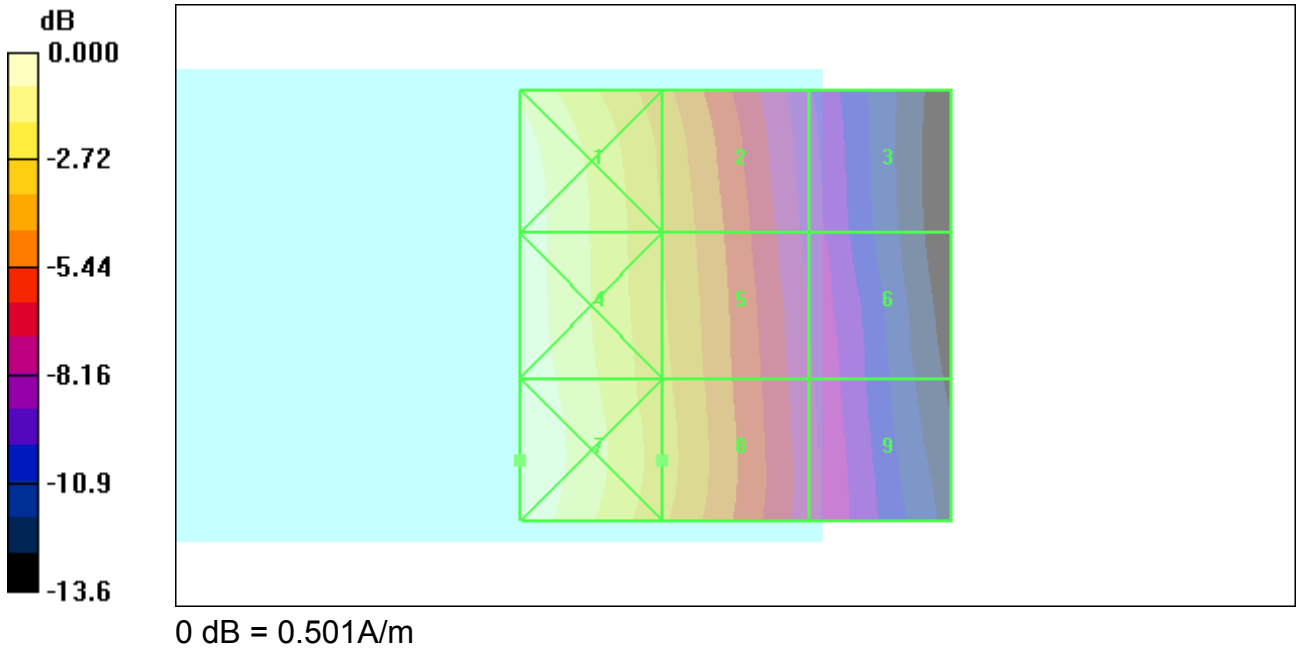
H Scan - M-ch/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.347 A/m
Probe Modulation Factor = 2.85
Device Reference Point: 0.000, 0.000, -6.30 mm
Reference Value = 0.096 A/m; Power Drift = -0.008 dB
Hearing Aid Near-Field Category: M4 (AWF -5 dB)

Peak H-field in A/m

Grid 1 **0.480 M3**	Grid 2 **0.331 M4**	Grid 3 **0.190 M4**
Grid 4 **0.491 M3**	Grid 5 **0.339 M4**	Grid 6 **0.201 M4**
Grid 7 **0.501 M3**	Grid 8 **0.347 M4**	Grid 9 **0.206 M4**

Cursor:
Total = 0.501 A/m
H Category: M3
Location: 25, 18, 8.7 mm



0 dB = 0.501A/m

Date/Time: 12/15/2009 5:00:36 PM

Test Laboratory: Compliance Certification Services

GSM850 HAC_H3DV6_Device With Inductive Cover

DUT: Palm; Type: P121UNA; Serial: 8054

Communication System: GSM850; Frequency: 848.8 MHz;Duty Cycle: 1:8
Medium parameters used: σ = 0 mho/m, ε_r = 1; ρ = 1 kg/m^3
Phantom section: RF Section

DASY4 Configuration:
- Probe: H3DV6 - SN6157; ; Calibrated: 2/10/2009
- Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn500; Calibrated: 9/15/2009
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 100x
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - H-ch/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

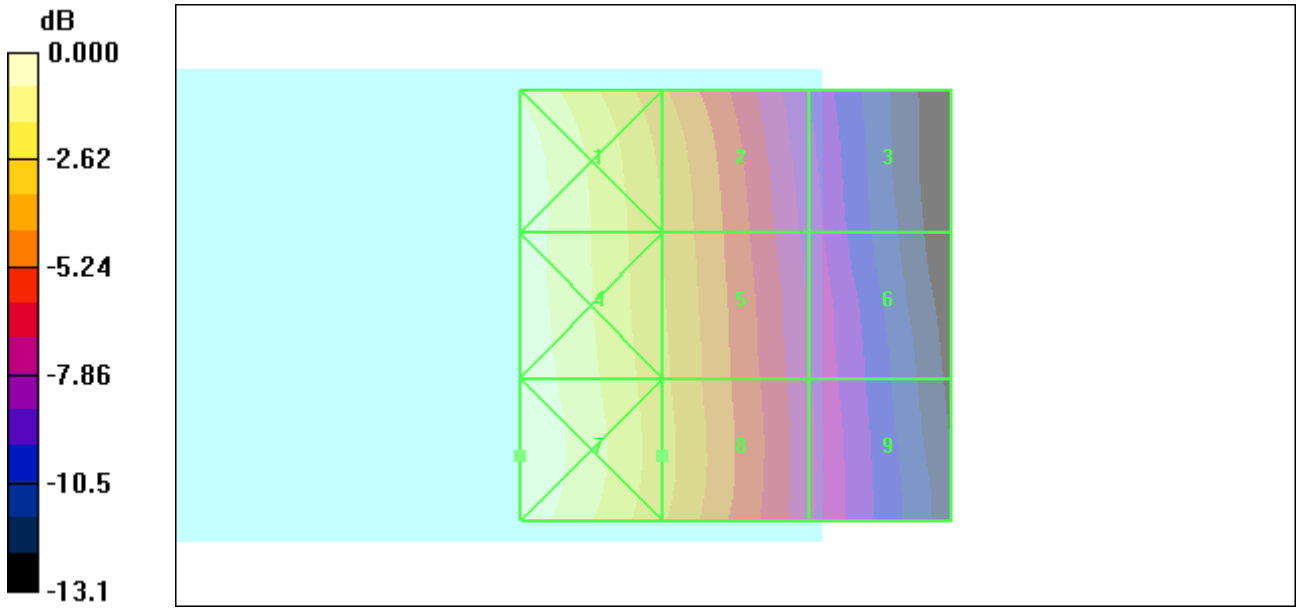
Maximum value of peak Total field = 0.351 A/m
Probe Modulation Factor = 2.85
Device Reference Point: 0.000, 0.000, -6.30 mm
Reference Value = 0.099 A/m; Power Drift = -0.006 dB

Hearing Aid Near-Field Category: M4 (AWF -5 dB)

Peak H-field in A/m

Grid 1 **0.484 M3**	Grid 2 **0.337 M4**	Grid 3 **0.197 M4**
Grid 4 **0.493 M3**	Grid 5 **0.346 M4**	Grid 6 **0.206 M4**
Grid 7 **0.503 M3**	Grid 8 **0.351 M4**	Grid 9 **0.211 M4**

Cursor:
Total = 0.503 A/m
H Category: M3
Location: 25, 17.5, 8.7 mm



0 dB = 0.503A/m

Date/Time: 12/15/2009 2:44:29 PM

Test Laboratory: Compliance Certification Services

GSM1900 HAC_H3DV6_Device_Final

DUT: Palm; Type: P121UNA; Serial: 8054

Communication System: GSM1900; Frequency: 1850.2 MHz;Duty Cycle: 1:8
Medium parameters used: σ = 0 mho/m, ε_r = 1; ρ = 1 kg/m^3
Phantom section: RF Section

DASY4 Configuration:
- Probe: H3DV6 - SN6157; ; Calibrated: 2/10/2009
- Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn500; Calibrated: 9/15/2009
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 100x
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

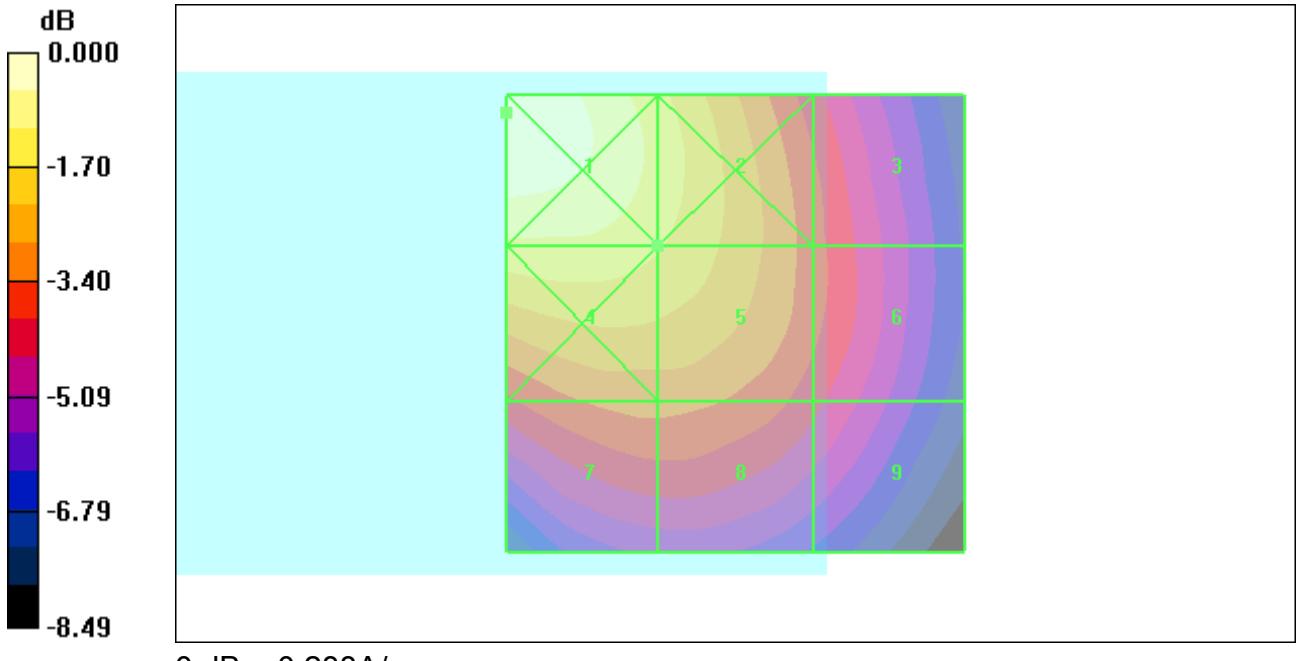
H Scan - L-ch/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.238 A/m
Probe Modulation Factor = 2.75
Device Reference Point: 0.000, 0.000, -6.30 mm
Reference Value = 0.083 A/m; Power Drift = 0.028 dB
Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak H-field in A/m

Grid 1 **0.288 M2**	Grid 2 **0.248 M3**	Grid 3 **0.188 M3**
Grid 4 **0.250 M3**	Grid 5 **0.238 M3**	Grid 6 **0.189 M3**
Grid 7 **0.200 M3**	Grid 8 **0.200 M3**	Grid 9 **0.175 M3**

Cursor:
Total = 0.288 A/m
H Category: M2
Location: 25, -23, 8.7 mm



0 dB = 0.288A/m

Date/Time: 12/15/2009 2:50:08 PM

Test Laboratory: Compliance Certification Services

GSM1900 HAC_H3DV6_Device_Final

DUT: Palm; Type: P121UNA; Serial: 8054

Communication System: GSM1900; Frequency: 1880 MHz;Duty Cycle: 1:8
Medium parameters used: σ = 0 mho/m, ε_r = 1; ρ = 1 kg/m^3
Phantom section: RF Section

DASY4 Configuration:
- Probe: H3DV6 - SN6157; ; Calibrated: 2/10/2009
- Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn500; Calibrated: 9/15/2009
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 100x
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

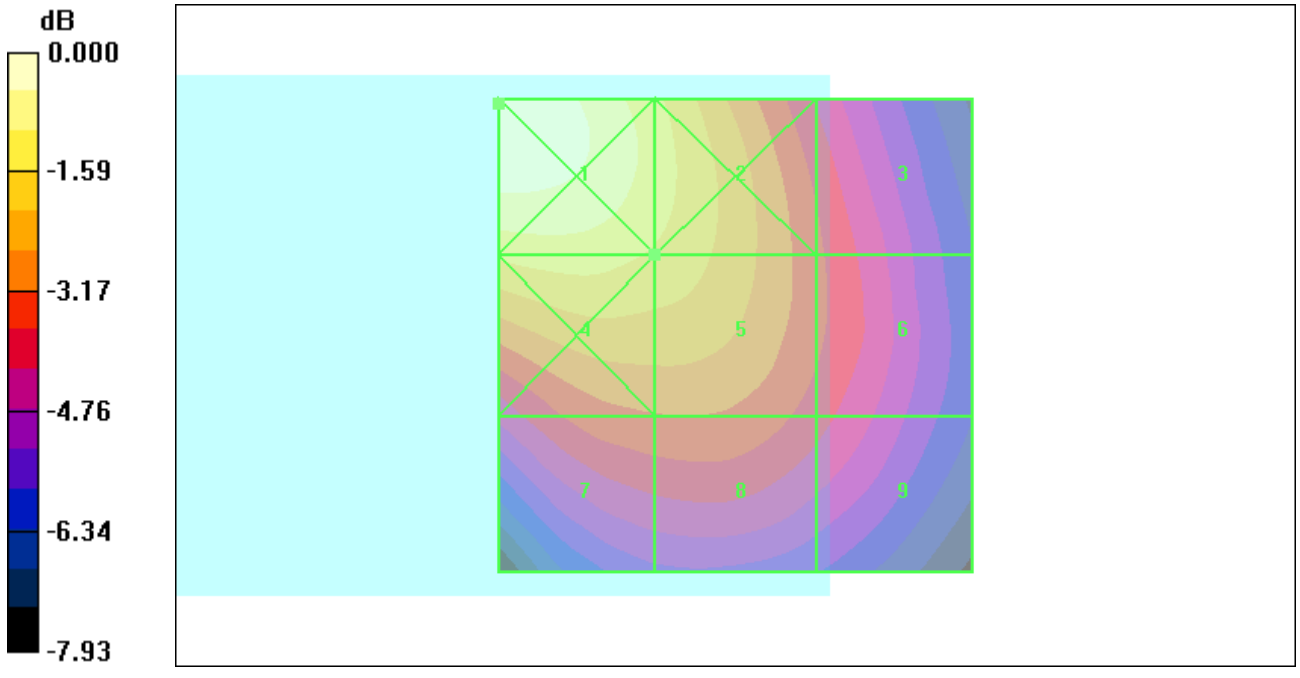
H Scan - M-ch/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.233 A/m
Probe Modulation Factor = 2.75
Device Reference Point: 0.000, 0.000, -6.30 mm
Reference Value = 0.082 A/m; Power Drift = 0.001 dB
Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak H-field in A/m

Grid 1 **0.282 M2**	Grid 2 **0.244 M3**	Grid 3 **0.187 M3**
Grid 4 **0.242 M3**	Grid 5 **0.233 M3**	Grid 6 **0.188 M3**
Grid 7 **0.195 M3**	Grid 8 **0.196 M3**	Grid 9 **0.178 M3**

Cursor:
Total = 0.282 A/m
H Category: M2
Location: 25, -24.5, 8.7 mm



Date/Time: 12/15/2009 2:56:26 PM

Test Laboratory: Compliance Certification Services

GSM1900 HAC_H3DV6_Device_Final

DUT: Palm; Type: P121UNA; Serial: 8054

Communication System: GSM1900; Frequency: 1909.8 MHz;Duty Cycle: 1:8
Medium parameters used: σ = 0 mho/m, ε_r = 1; ρ = 1 kg/m^3
Phantom section: RF Section

DASY4 Configuration:
- Probe: H3DV6 - SN6157; ; Calibrated: 2/10/2009
- Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn500; Calibrated: 9/15/2009
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 100x
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

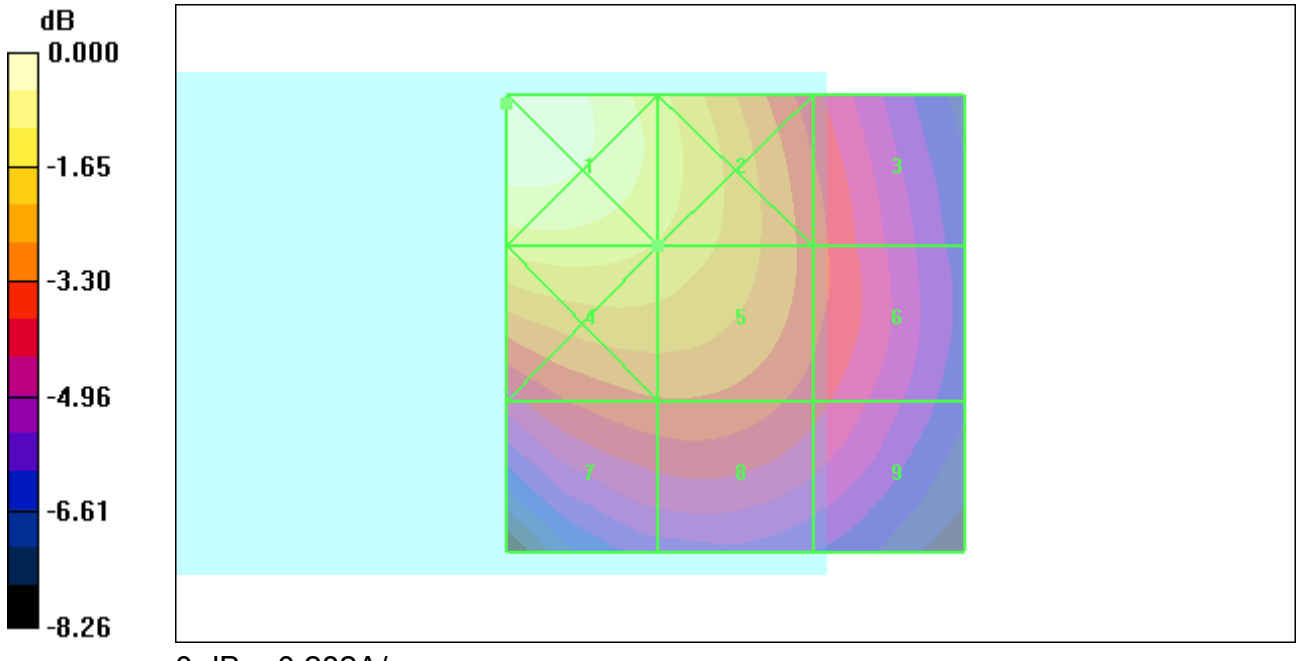
H Scan - H-ch/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.232 A/m
Probe Modulation Factor = 2.75
Device Reference Point: 0.000, 0.000, -6.30 mm
Reference Value = 0.082 A/m; Power Drift = 0.032 dB
Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak H-field in A/m

Grid 1 **0.282 M2**	Grid 2 **0.243 M3**	Grid 3 **0.187 M3**
Grid 4 **0.242 M3**	Grid 5 **0.232 M3**	Grid 6 **0.187 M3**
Grid 7 **0.192 M3**	Grid 8 **0.192 M3**	Grid 9 **0.175 M3**

Cursor:
Total = 0.282 A/m
H Category: M2
Location: 25, -24, 8.7 mm



0 dB = 0.282A/m

Date/Time: 12/15/2009 2:19:43 PM

Test Laboratory: Compliance Certification Services

GSM1900 HAC_H3DV6_Device with inductive cover

DUT: Palm; Type: P121UNA; Serial: 8054

Communication System: GSM1900; Frequency: 1850.2 MHz;Duty Cycle: 1:8
Medium parameters used: σ = 0 mho/m, ε_r = 1; ρ = 1 kg/m^3
Phantom section: RF Section

DASY4 Configuration:
- Probe: H3DV6 - SN6157; ; Calibrated: 2/10/2009
- Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn500; Calibrated: 9/15/2009
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 100x
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - L-ch/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

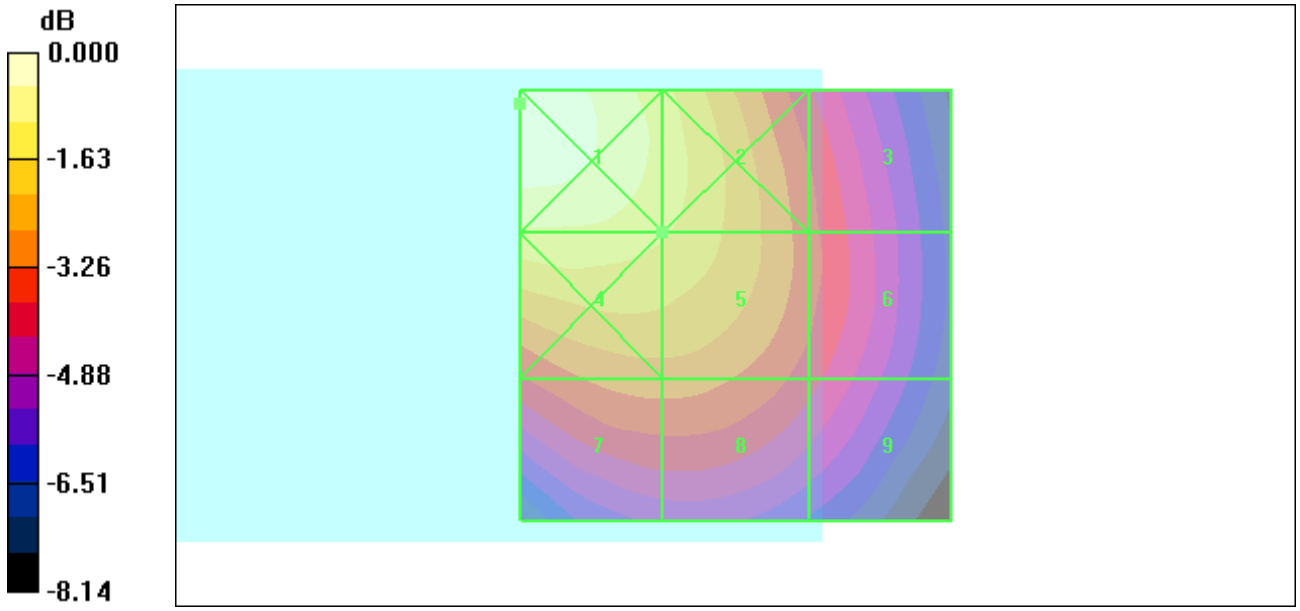
Maximum value of peak Total field = 0.225 A/m
Probe Modulation Factor = 2.75
Device Reference Point: 0.000, 0.000, -6.30 mm
Reference Value = 0.080 A/m; Power Drift = -0.015 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak H-field in A/m

Grid 1 **0.269 M2**	Grid 2 **0.233 M3**	Grid 3 **0.178 M3**
Grid 4 **0.236 M3**	Grid 5 **0.225 M3**	Grid 6 **0.179 M3**
Grid 7 **0.191 M3**	Grid 8 **0.191 M3**	Grid 9 **0.168 M3**

Cursor:
Total = 0.269 A/m
H Category: M2
Location: 25, -23.5, 8.7 mm



0 dB = 0.269A/m

Date/Time: 12/15/2009 2:28:03 PM

Test Laboratory: Compliance Certification Services

GSM1900 HAC_H3DV6_Device with inductive cover

DUT: Palm; Type: P121UNA; Serial: 8054

Communication System: GSM1900; Frequency: 1880 MHz;Duty Cycle: 1:8
Medium parameters used: σ = 0 mho/m, ε_r = 1; ρ = 1 kg/m^3
Phantom section: RF Section

DASY4 Configuration:
- Probe: H3DV6 - SN6157; ; Calibrated: 2/10/2009
- Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn500; Calibrated: 9/15/2009
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 100x
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - M-ch/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

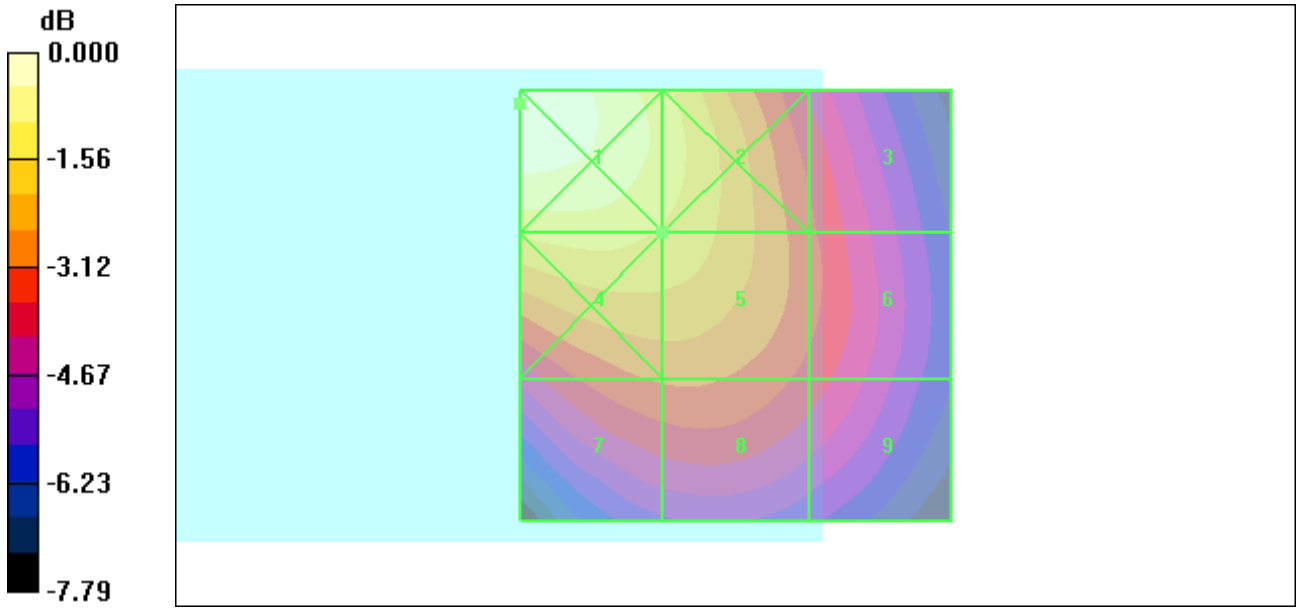
Maximum value of peak Total field = 0.222 A/m
Probe Modulation Factor = 2.75
Device Reference Point: 0.000, 0.000, -6.30 mm
Reference Value = 0.079 A/m; Power Drift = 0.032 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak H-field in A/m

Grid 1 **0.267 M2**	Grid 2 **0.233 M3**	Grid 3 **0.179 M3**
Grid 4 **0.230 M3**	Grid 5 **0.222 M3**	Grid 6 **0.181 M3**
Grid 7 **0.188 M3**	Grid 8 **0.189 M3**	Grid 9 **0.172 M3**

Cursor:
Total = 0.267 A/m
H Category: M2
Location: 25, -23.5, 8.7 mm



0 dB = 0.267A/m

Date/Time: 12/15/2009 2:34:33 PM

Test Laboratory: Compliance Certification Services

GSM1900 HAC_H3DV6_Device with inductive cover

DUT: Palm; Type: P121UNA; Serial: 8054

Communication System: GSM1900; Frequency: 1909.8 MHz;Duty Cycle: 1:8
Medium parameters used: σ = 0 mho/m, ε_r = 1; ρ = 1 kg/m^3
Phantom section: RF Section

DASY4 Configuration:
- Probe: H3DV6 - SN6157; ; Calibrated: 2/10/2009
- Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn500; Calibrated: 9/15/2009
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 100x
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - H-ch/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

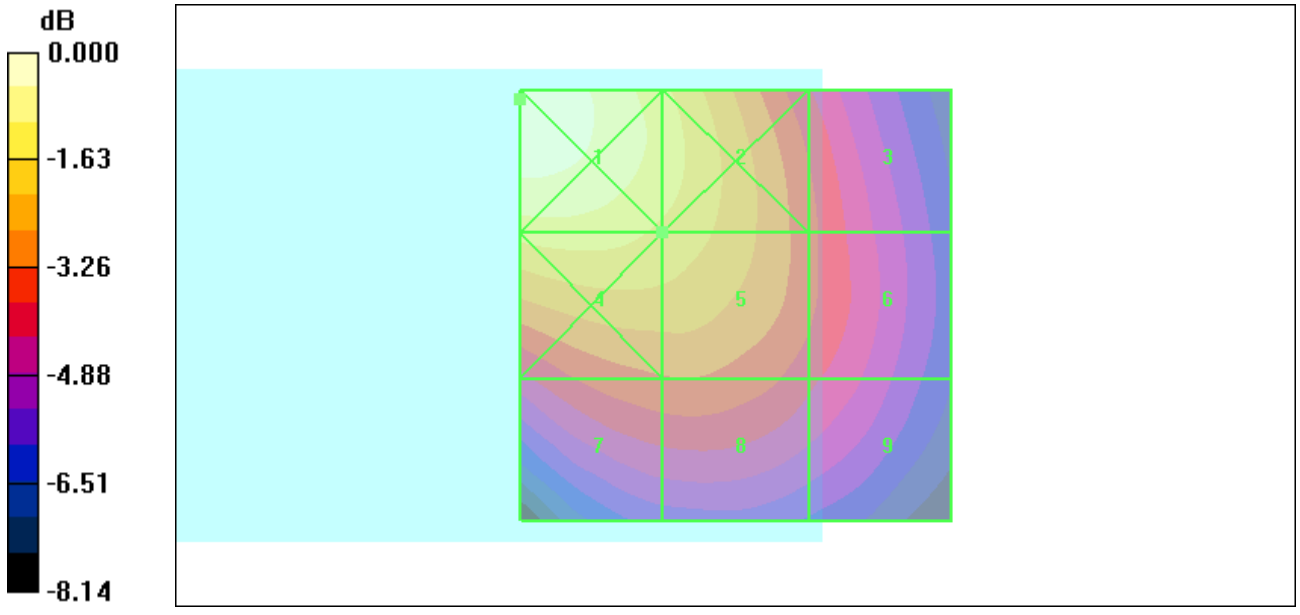
Maximum value of peak Total field = 0.223 A/m
Probe Modulation Factor = 2.75
Device Reference Point: 0.000, 0.000, -6.30 mm
Reference Value = 0.080 A/m; Power Drift = -0.035 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak H-field in A/m

Grid 1 **0.272 M2**	Grid 2 **0.234 M3**	Grid 3 **0.180 M3**
Grid 4 **0.234 M3**	Grid 5 **0.223 M3**	Grid 6 **0.180 M3**
Grid 7 **0.186 M3**	Grid 8 **0.187 M3**	Grid 9 **0.168 M3**

Cursor:
Total = 0.272 A/m
H Category: M2
Location: 25, -24, 8.7 mm



0 dB = 0.272A/m